The RF Line

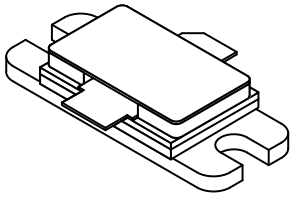
Microwave Pulse Power Transistors

. . . designed for 1025–1150 MHz pulse common base amplifier applications such as TCAS, TACAN and Mode–S transmitters.

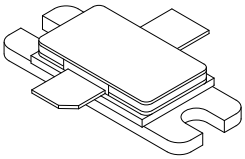
- Guaranteed Performance @ 1090 MHz
  Output Power = 500 Watts Peak
  Gain = 8.5 dB Min, 9.0 dB (Typ)
- 100% Tested for Load Mismatch at All Phase Angles with 10:1 VSWR
- Hermetically Sealed Industry Package
- Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Internal Input and Output Matching
- Characterized with 10 µs, 1% Duty Cycle Pulses

MRF10500
MRF10501

500 W (PEAK)
1025–1150 MHz
MICROWAVE POWER TRANSISTORS
NPN SILICON



CASE 355D–02, STYLE 1
MRF10500



CASE 355H–01, STYLE 1
MRF10501

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CES}	65	Vdc
Collector–Base Voltage	V_{CBO}	65	Vdc
Emitter–Base Voltage	V_{EBO}	3.5	Vdc
Collector Current — Peak (1)	I_C	29	Adc
Total Device Dissipation @ T_C = 25°C (1), (2) Derate above 25°C	P_D	1460 8.3	Watts W/°C
Storage Temperature Range	T_{stg}	–65 to +200	°C
Junction Temperature	T_J	200	°C

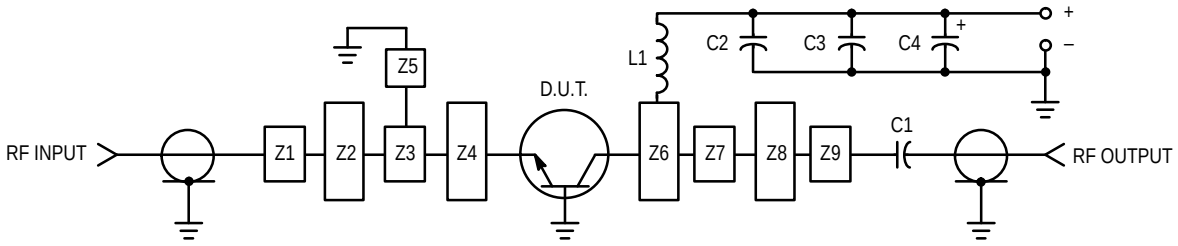
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (3)	$R_{\theta JC}$	0.12	°C/W

NOTES:
1. Under pulse RF operating conditions.
2. These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as pulsed RF amplifiers.
3. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques. (Worst case θ_{JC} value measured @ 32 µs, 2%.)

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I_C = 60 mAdc, V_{BE} = 0)	$V_{(BR)CES}$	65	—	—	Vdc
Collector–Base Breakdown Voltage (I_C = 60 mAdc, I_E = 0)	$V_{(BR)CBO}$	65	—	—	Vdc
Emitter–Base Breakdown Voltage (I_E = 10 mAdc, I_C = 0)	$V_{(BR)EBO}$	3.5	—	—	Vdc
Collector Cutoff Current (V_{CB} = 36 Vdc, I_E = 0)	I_{CBO}	—	—	25	mAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 5.0 Adc, V_{CE} = 5.0 Vdc)	h_{FE}	20	—	—	—
FUNCTIONAL TESTS					
Common–Base Amplifier Power Gain (V_{CC} = 50 Vdc, P_{out} = 500 W Peak, f = 1090 MHz)	G_{PB}	8.5	9.0	—	dB
Collector Efficiency (V_{CC} = 50 Vdc, P_{out} = 500 W Peak, f = 1090 MHz)	η	40	45	—	%
Load Mismatch (V_{CC} = 50 Vdc, P_{out} = 500 W Peak, f = 1090 MHz, VSWR = 10:1 All Phase Angles)	ψ	No Degradation in Output Power			



C1 — 82 pF 100 Mil Chip Capacitor
C2 — 39 pF 100 Mil Chip Capacitor
C3 — 0.1 μF
C4 — 100 μF, 100 Vdc, Electrolytic
L1 — 3 Turns #18 AWG, 1/8″ ID, 0.18 Long

Z1–Z9 — Microstrip, See Details
Board Material — Teflon, Glass Laminate
Dielectric Thickness = 0.030″
ε_r = 2.55, 2 Oz. Copper

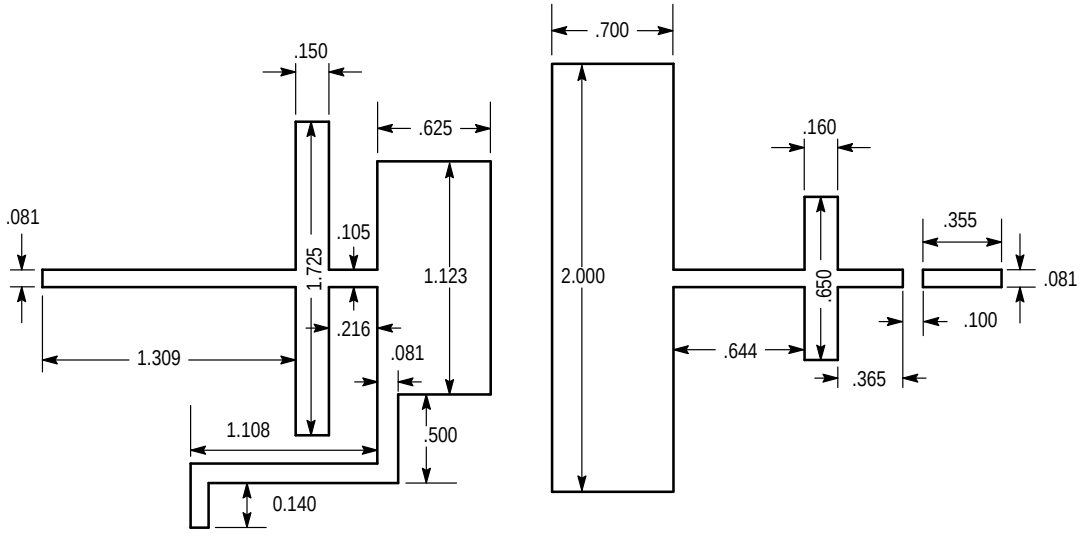


Figure 1. Test Circuit

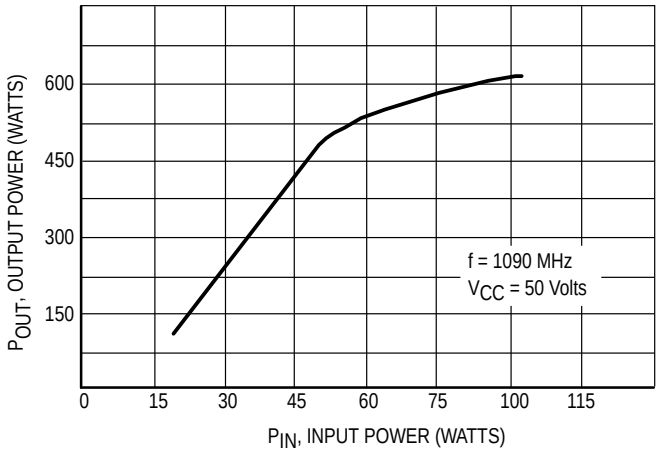
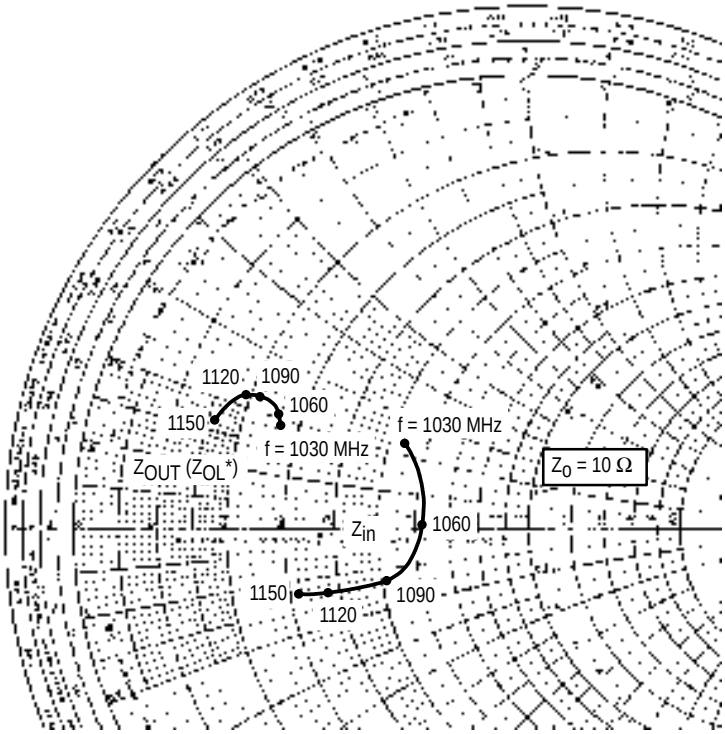


Figure 2. Output Power versus Input Power



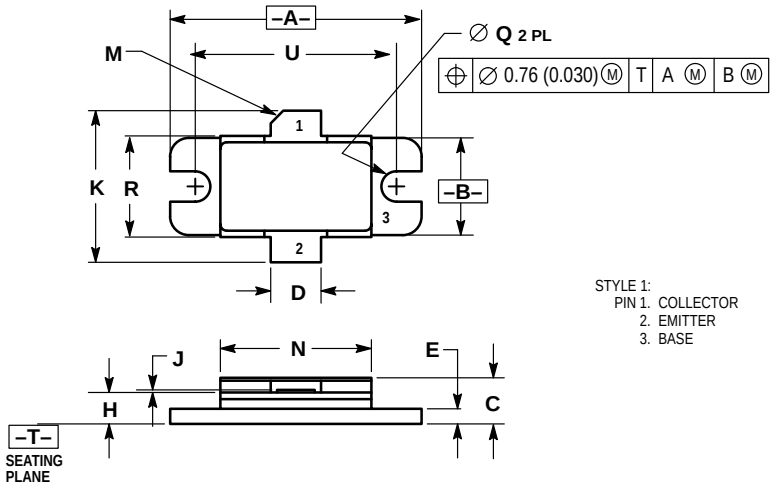
P_{OUT} = 500 W Pk V_{CC} = 50 V

f MHz	Z_{in} OHMS	Z_{OL}* (Z_{OUT}) OHMS
1030	5.3 + j2.25	2.6 + j1.89
1060	6.2 + j0.2	2.56 + j2.0
1090	5.2 – j1.4	2.12 + j2.2
1120	3.7 – j1.35	1.9 + j2.15
1150	3.15 – j1.3	1.6 + j1.62

Z_{OL}* is the conjugate of the optimum load impedance into which the device operates at a given output power voltage and frequency.

Figure 3. Series Equivalent Input/Output Impedances

PACKAGE DIMENSIONS

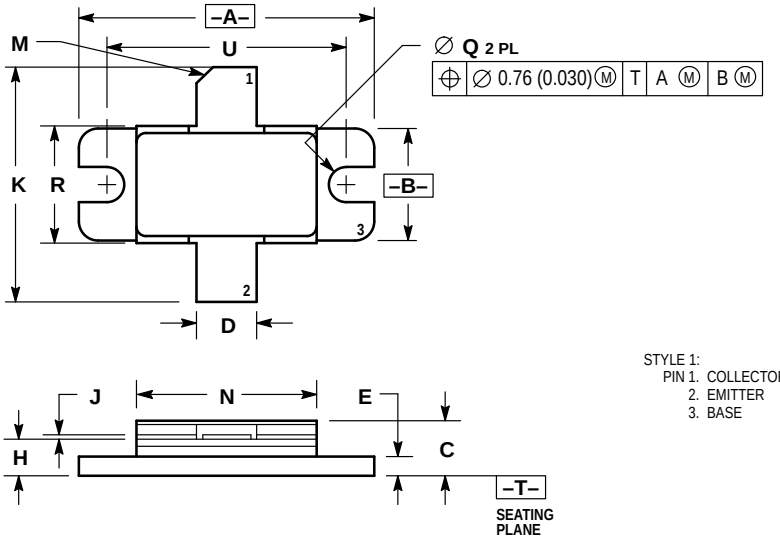


STYLE 1:
PIN 1. COLLECTOR
2. EMITTER
3. BASE

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.990	1.010	25.15	25.65
B	0.375	0.395	9.53	10.03
C	0.150	0.165	3.81	4.19
D	0.195	0.205	4.95	5.21
E	0.055	0.065	1.40	1.65
H	0.120	0.130	3.05	3.30
J	0.003	0.006	0.08	0.15
K	0.570	0.630	14.48	16.00
M	45 ° REF		45 ° REF	
N	0.590	0.610	14.99	15.49
Q	0.115	0.125	2.92	3.18
R	0.395	0.405	10.03	10.29
U	0.800 BSC		20.32 BSC	

CASE 355D–02
ISSUE B
MRF10500



STYLE 1:
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	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
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B	0.375	0.395	9.53	10.03
C	0.150	0.165	3.81	4.19
D	0.195	0.205	4.95	5.21
E	0.055	0.065	1.40	1.65
H	0.120	0.130	3.05	3.30
J	0.003	0.006	0.08	0.15
K	0.780	0.820	19.81	20.83
M	45 ° REF		45 ° REF	
N	0.590	0.610	14.99	15.49
Q	0.115	0.125	2.92	3.18
R	0.395	0.405	10.03	10.29
U	0.800 BSC		20.32 BSC	

CASE 355H–01
ISSUE A
MRF10501

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